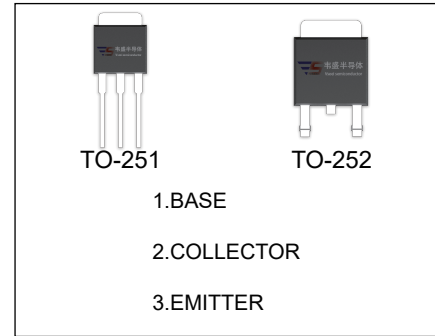


MJD117 TRANSISTOR (PNP)

FEATURES

- High DC Current Gain
- Low Collector-Emitter Saturation Voltage
- Complementary to MJD112



MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CB0}	Collector-Base Voltage	-100	V
V_{CEO}	Collector-Emitter Voltage	-100	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-2	A
P_C	Collector Power Dissipation	1.75	W
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	71	$^{\circ}\text{C}/\text{W}$
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-1\text{mA}, I_E=0$	-100			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}^*$	$I_C=-30\text{mA}, I_B=0$	-100			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-5\text{mA}, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-80\text{V}, I_E=0$			-10	μA
Collector cut-off current	I_{CEO}	$V_{CE}=-80\text{V}, I_B=0$			-10	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5\text{V}, I_C=0$			-2	mA
DC current gain	$h_{FE(1)}^*$	$V_{CE}=-3\text{V}, I_C=-0.5\text{A}$	500			
	$h_{FE(2)}^*$	$V_{CE}=-3\text{V}, I_C=-2\text{A}$	1000		12000	
	$h_{FE(3)}^*$	$V_{CE}=-3\text{V}, I_C=-4\text{A}$	200			
Collector-emitter saturation voltage	$V_{CE(sat)}^*$	$I_C=-2\text{A}, I_B=-8\text{mA}$			-2	V
		$I_C=-4\text{A}, I_B=-40\text{mA}$			-3	V
Base-emitter saturation voltage	$V_{BE(sat)}^*$	$I_C=-4\text{A}, I_B=-40\text{mA}$			-4	V
Base-emitter voltage	V_{BE}	$V_{CE}=-3\text{V}, I_C=-2\text{A}$			-2.8	V
Collector output capacitance	C_{ob}	$V_{CB}=-10\text{V}, I_E=0, f=0.1\text{MHz}$			200	pF
Transition frequency	f_T	$V_{CE}=-10\text{V}, I_C=-0.75\text{A}, f=1\text{MHz}$	25			MHz

*Pulse test